

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device comprising:

~~at least one set a plurality of sets~~ of complementarily operating first and second switching elements serially interposed between first and second main power supply terminals supplied with a dc voltage;

~~at least one set a plurality of control circuit circuits~~ driving/controlling said ~~at least one set~~ ~~plurality of sets~~ of first and second switching elements ~~respectively~~; and

a shunt resistor detecting a current flowing across said first and second main power supply terminals, wherein

each of said at least one plurality of control circuit circuits comprises:

at least one current detection circuit detecting a voltage generated by a current flowing to said shunt resistor and outputting a current abnormality signal indicating current abnormality when detected said voltage is in excess of a prescribed level, and

a fault circuit receiving said current abnormality signal output from said at least one current detection circuit and outputting a stop signal for stopping operation of at least one of said first and second switching elements, corresponding to said current abnormality, and

~~the exterior of said at least one control circuit a different control circuit other than said control circuit to which itself belongs~~ while stopping operation of at least one of said first and second switching elements which is controlled by said control circuit to which itself belongs also by a signal, identical to said stop signal, input from the exterior of said at least one control circuit said stop signal input from said different control circuit.

Claim 2 (Currently Amended): The semiconductor device according to claim 1, wherein

 said at least one current detection circuit includes first and second current detection circuits, and

 said first current detection circuit is set lower in detected voltage ~~higher in detection~~ sensitivity than said second current detection circuit.

Claim 3 (Currently Amended): The semiconductor device according to claim 2, ~~comprising a plurality of said control circuits, and~~ ~~comprising a plurality of sets of said first and second switching elements in correspondence to said plurality of control circuits respectively,~~ wherein only one of said plurality of control circuits detects said voltage of said shunt resistor by said first current detection circuit while remaining said control circuit is electrically connected to said shunt resistor to detect said voltage of said shunt resistor by said second current detection circuit.

Claim 4 (Currently Amended): The semiconductor device according to claim 1, ~~comprising a plurality of said control circuits, and~~ ~~comprising a plurality of sets of said first and second switching elements in correspondence to said plurality of control circuits respectively,~~ wherein only one of said plurality of control circuits detects said voltage of said shunt resistor, outputs said stop signal and supplies the same to said fault circuit of remaining said control circuit.

Claim 5 (Original): The semiconductor device according to claim 1, wherein

said at least one control circuit further comprises:

a voltage detection circuit detecting a driving voltage supplied to said at least one control circuit and outputting a voltage reduction signal indicating voltage reduction when said driving voltage is below a prescribed level, and

said fault circuit outputs said stop signal when at least one of said voltage reduction signal and said current abnormality signal is output.

Claim 6 (Currently Amended): The semiconductor device according to claim 5,

wherein

said driving voltage is supplied to a control electrode of a low-potential side [[one]] of said at least one set of first and second switching elements also as a control voltage.

Claim 7 (Currently Amended): The semiconductor device according to claim 5,

wherein

said at least one current detection circuit includes first and second current detection circuits, and

said first current detection circuit is set lower in detected voltage higher in detection sensitivity than said second current detection circuit.

Claim 8 (Currently Amended): The semiconductor device according to claim 7,

~~comprising a plurality of said control circuits, and~~

~~comprising a plurality of sets of said first and second switching elements in correspondence to said plurality of control circuits respectively,~~ wherein

only one of said plurality of control circuits detects said voltage of said shunt resistor by said first current detection circuit while remaining said control circuit is electrically connected to said shunt resistor to detect said voltage of said shunt resistor by said second current detection circuit.

Claim 9 (Currently Amended): The semiconductor device according to claim 5,
~~comprising a plurality of said control circuits, and~~
~~comprising a plurality of sets of said first and second switching elements in~~
~~correspondence to said plurality of control circuits respectively, wherein~~
only one of said plurality of control circuits detects said voltage of said shunt resistor, outputs said stop signal and supplies the same to said fault circuit of remaining said control circuit.

IN THE DRAWINGS

The attached sheet of drawings includes changes to Figs. 8 and 9. This sheet, which includes Figs. 8 and 9, replaces the original sheet including Figs. 8 and 9.

Attachment: Replacement Sheet